

## isc N-Channel MOSFET Transistor

IPP60R125P6, IIPP60R125P6

### • FEATURES

- Static drain-source on-resistance:  $R_{DS(on)} \leq 0.125\Omega$
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • DESCRIPTION

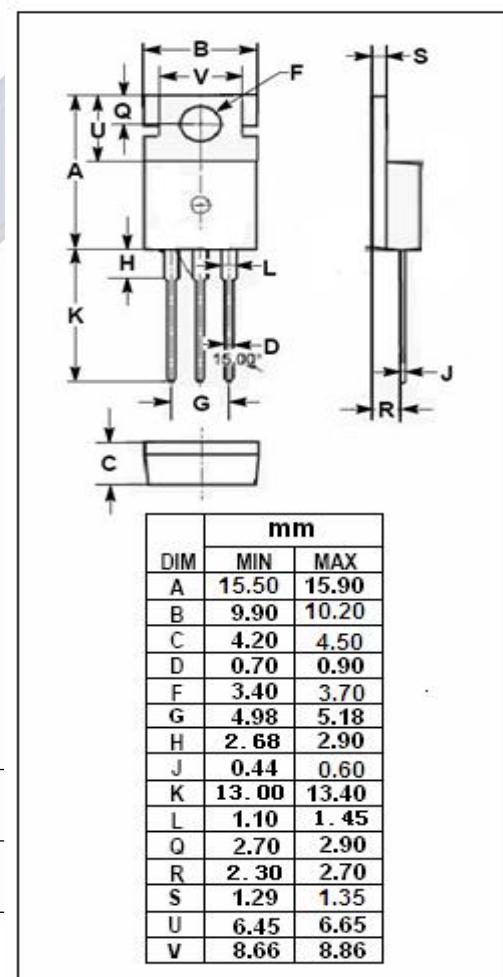
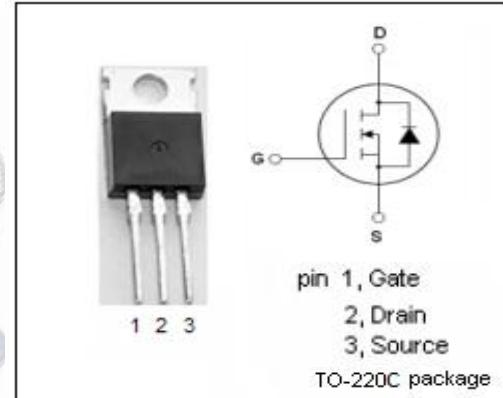
- Provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	30	A
$I_{DM}$	Drain Current-Single Pulsed	87	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	219	W
$T_j$	Max. Operating Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55~150	°C

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.57	°C/W
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	°C/W



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## ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}; \text{ID} = 1\text{mA}$	600			V
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}; \text{ID} = 0.96\text{mA}$	3.5		4.5	V
$\text{R}_{\text{DS(on)}}$	Drain-Source On-Resistance	$\text{V}_{\text{GS}}=10\text{V}; \text{ID}=11.6\text{A}$			0.125	$\Omega$
$\text{I}_{\text{GSS}}$	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=20\text{V}; \text{V}_{\text{DS}}=0\text{V}$			0.1	$\mu\text{A}$
$\text{I}_{\text{DSS}}$	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=600\text{V}; \text{V}_{\text{GS}}= 0\text{V}$			2	$\mu\text{A}$
$\text{V}_{\text{SD}}$	Diode forward voltage	$\text{I}_F=14.5\text{A}; \text{V}_{\text{GS}} = 0\text{V}$		0.9		V